Old Company Name in Catalogs and Other Documents

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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)
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SILICON POWER TRANSISTOR NTC1860

HIGH SPEED HIGH VOLTAGE SWITCHING NPN SILICON EPITAXIAL TRANSISTOR

Industrial Use

DESCRIPTION

The state of

Suitable for switching regulator, DC-DC converter and ultrasonic appliance applications.

PACKAGE DIMENSIONS in millimeters (inches)

φ9.40MAX. (φ0.37 MAX.) φ8.50MAX. (φ0.335 MAX.) φ8.50MAX. (φ0.031) (γννογο (γννογο) (γν

- 1. Emitter
- 2. Base
- 3. Collector (Case)

EIAJ :TC-5,TB-5B JEDEC:TO-205MD (TO-39) IEC :C4,B4B

FEATURES

- High speed switching.
- Low collector saturation voltage.
- Specified of reverse biased S.O.A. with inductive loads.

ABSOLUTE MAXIMUM RATINGS

| Maximum Voltages and Currents (Ta = 25°C) | • | | |
|---|-----------------------|-------------|------|
| Collector to Emitter Voltage | VCEX | 150 | ٧ |
| Collector to Emitter Sustaining Voltage | VCEO(SUS) | 100 | ٧ |
| Collector to Emitter Sustaining Voltage | VCEX(SUS) | 150 | ٧ |
| Emitter to Base Voltage | VEBO | 7.0 | ٧ |
| Continuous Collector Current | (C(DC) | 2.0 | Α |
| Peak Collector Current* | (C(pulse) | 4.0 | Α |
| Continuous Base Current | IB(DC) | 1.0 | Α |
| Peak Base Current* | B(pulse) | 2.0 | A |
| Maximum Power Dissipations | | | |
| Total Power Dissipation | PT(Tc=25°C) | 15 | W |
| Total Power Dissipation | PT(Tc=100°C) | 8.6 | W |
| Total Power Dissipation | PT(Ta=25°C) | 1.0 | W |
| Maximum Temperatures | | | |
| Junction Temperature | Тj | 200 | °C |
| Storage Temperature | T _{stg} | -65 to +200 | °C |
| Lead Temperature 1/8 inch from case for 10 seconds | TL | 260 | °C |
| Thermal Resistances | | | |
| Junction to Case | R _{th} (j-c) | 11.7 | °C/W |
| Junction to Ambient | R _{th} (j-a) | 175 | °C/W |

* Pulsed PW \leq 300 μ s, duty cycle \leq 10%

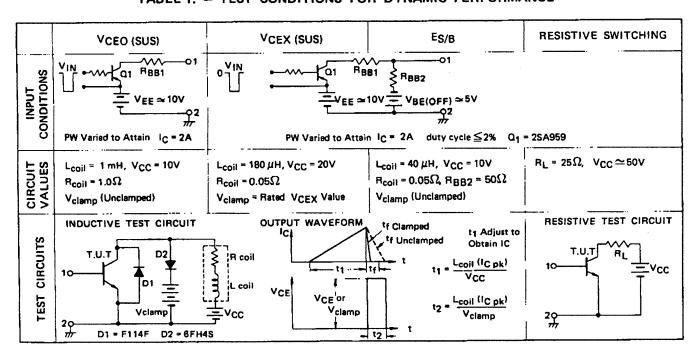


ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|------------------------------------|----------------------|-------|----------|-----------|-------|--|
| Collector to Emitter | VCEO(SUS) | 100 | | | V | Table 1. I _C = 2A, I _{B1} = 0.2A, L = 1 mH |
| Sustaining Voltage | VCEX(SUS)1 | 150 | † - · | | V | Table 1. IC = 2A, IB1 = -IB2 = 0.2A, |
| - | | | | | 1 | V _{clamp} = Rated V _{CEX} , Ta = 125°C |
| | VCEX(SUS)2 | 100 | · —- | | v | Table 1. IC = 4A, IB1 = 0.4A IB2 = -0.2A, |
| | | | 1 | | | V _{clamp} = Rated V _{CEX} , Ta = 125°C |
| Collector Cutoff Current | ICER | | | 100 | mA | VCE = 150V, RBE = 500Ω, Ta = 125°C |
| | CEX | | Ţ ·—- | 1.0 | μΑ | VCE = 150V, VBE(OFF) = 1.5V |
| | ICEX | | | 100 | μΑ | $V_{CE} = 150V$, $V_{BE(OFF)} = 1.5V$, |
| | ' | | i | : | ' | Ta = 125°C |
| Emitter Cutoff Current | EBO | | j | 1.0 | μΑ | VEB = 7.0V, 1C = 0 |
| Second Breakdown Collector Current | · | 0.75 | | | A | t = 1.0 s, VCE = 20V, Tc = 25°C |
| Second Breakdown Energy | E _{S/B} | 80 | <u> </u> | 7 | μJ | IC = 2A, IB1 = 0.2A, VBE(OFF) = 5V |
| DC Current Gain | hFE1 | 30 | | 160 | : | VCE = 5V, IC = 0.1A ** |
| | hFE2 | 20 | • | ļ <u></u> | i | VCE = 5V, IC = 2.0A ** |
| Collector Saturation Voltage | V _{CE(sat)} | | | 1.0 | ' V | IC = 2A, IB = 0.2A ** |
| | VCE(sat) | | | 1.5 | . v _ | I _C = 2A, I _B = 0.2A Ta = 125°C ** |
| Base Saturation Voltage | VBE(sat) | | | 1.5 | i v | IC = 2A, IB = 0.2A ** |
| | VBE(sat) | • | | 1.5 | V | IC = 2A, IB = 0.2A, Ta = 125°C ** |
| Gain Bandwidth Product | f _T | 50 | | T | MHz | V _{CE} = 10V, I _C = 50 mA, f _o =3.0 MHz, T _c =25°C |
| Output Capacitance | Cob | | | 100 | ρF | VCB = 10V, fo = 1.0 MHz |
| Delay Time | ^t d | | | 0.1 | μs | Resistive Load (Table 1.) |
| Rise Time | tr | | i. | 0.4 | μs | |
| | t _r | | | 1.2 | μs | Ta = 125°C I _C = 2A, I _{B1} = -I _{B2} = 0.2A |
| Storage Time | tstg | | ! | 1.0 | μs | $R_L=25\Omega$, $V_{CC}\simeq 50V$ |
| | t _{stg} | · ··- | | 2.0 | μs | Ta = 125°C PW ≃ 50μs, dusy cycle ≤ 2% |
| Fall Time | tf | · | | 0.3 | μs | · |
| | tf | | i | 1.2 | μs | Ta = 125°C |

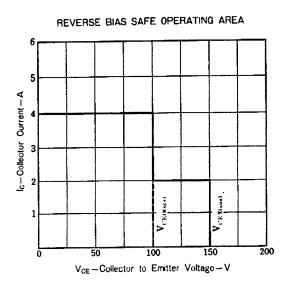
^{**} PW \leq 350 μ s, duty cycle \leq 2%

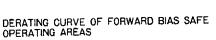
TABLE 1. - TEST CONDITIONS FOR DYNAMIC PERFORMANCE

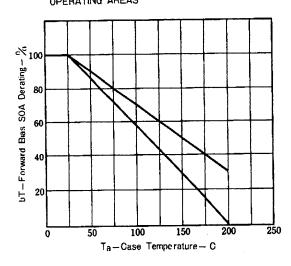




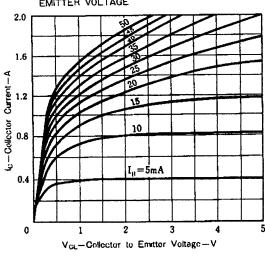
TYPICAL CHARACTERISTICS (Ta=25°C)



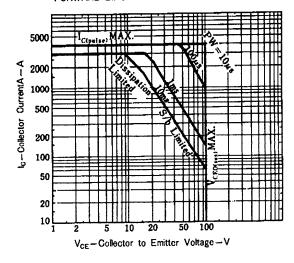




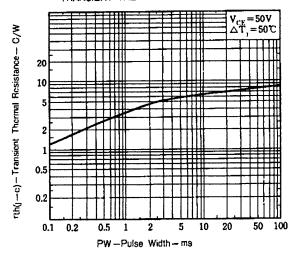
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



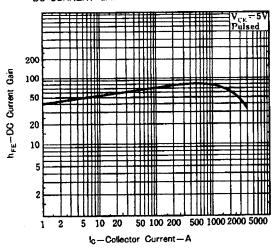
FORWARD BIAS SAFE OPERATING AREAS



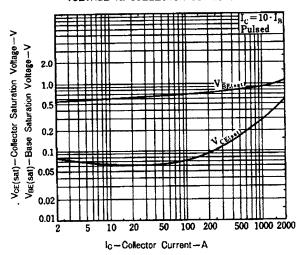
TRANSIENT THERMAL RESISTANCE



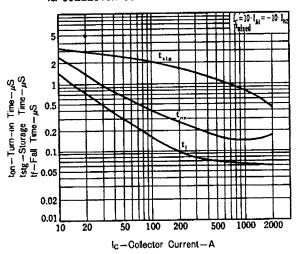
DC CURRENT GAIN vs. COLLECTOR CURRENT

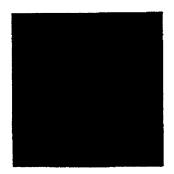


BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT





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